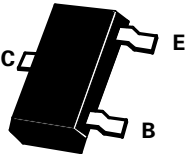


SOT23 PNP SILICON PLANAR HIGH SPEED TRANSISTOR

ISSUE 2 - SEPTEMBER 1995

BSS65

PARTMARKING DETAIL — BSS65 - L1
BSS65R - L5



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-12	V
Collector-Emitter Voltage	V_{CEO}	-12	V
Emitter-Base Voltage	V_{EBO}	-4	V
Peak Pulse Current	I_{CM}	-200	mA
Continuous Collector Current	I_C	-100	mA
Base Current	I_B	-50	mA
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{TOT}	330	mW
Operating and Storage Temperature Range	$t_j; t_{stg}$	-55 to +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Breakdown Voltages	$V_{(BR)CEO}$	-12			V	$I_C = -10mA$
	$V_{(BR)CBO}$	-12			V	$I_C = -10\mu A$ *
	$V_{(BR)EBO}$	-4			V	$I_E = -10\mu A$
Cut-Off Currents	I_{CBO}			-100	nA	$V_{CB} = -6V, I_E = 0$
	I_{EBO}			-100	nA	$V_{EB} = -4V, I_C = 0$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.15	V	$I_C = -10mA, I_B = -1mA$
				-0.25	V	$I_C = -30mA, I_B = -3mA$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	-0.75		-0.98	V	$I_C = -10mA, I_B = -1mA$
		-0.82		-1.20	V	$I_C = -30mA, I_B = -3mA$
Static Forward Current Transfer Ratio	h_{FE}	30		150		$I_C = -10mA, V_{CE} = -0.3V$
		40				$I_C = -30mA, V_{CE} = -0.5V$
Transition Frequency	f_T	400			MHz	$I_C = -30mA, V_{CE} = -10V, f = 100MHz$
Collector-Base Capacitance	C_{obo}			6	pF	$V_{CB} = -5V, I_E = 0, f = 1MHz$
Emitter Base Capacitance	C_{ebo}			6	pF	$V_{EB} = -0.5V, I_C = 0, f = 1MHz$
Switching Times	t_{on}		23	60	nS	$I_C = -30mA$
	t_{off}		34	90	nS	$I_{B1} = -I_{B2} = -1.5mA$ $V_{CC} = -10V$

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